

P-CHANNEL J-FET

Equivalent To MIL-PRF-19500/295

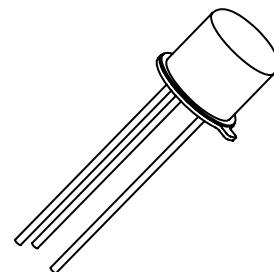
DEVICES
2N2608
LEVELS
MQ = JAN Equivalent
ABSOLUTE MAXIMUM RATINGS (T_C = +25°C unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Gate-Source Voltage	V _{GSS}	30	V
Power Dissipation ⁽¹⁾ T _A = +25°C	P _D	300	mW
Operating Junction & Storage Temperature Range	T _{op} , T _{stg}	-65 to + 200	°C

 (1) Derate linearly 1.71 mW/°C for T_A > +25°C.

ELECTRICAL CHARACTERISTICS (T_A = +25°C, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate-Source Breakdown Voltage V _{DS} = 0, I _G = 1.0µA dc	V _{(BR)GSS}	30		Vdc
Gate Reverse Current V _{DS} = 0, V _{GS} = 30V dc V _{DS} = 0, V _{GS} = 15V dc	I _{GSS}		10 7.5	nA
Drain Current V _{GS} = 0V dc, V _{DS} = 5.0V dc	I _{DSS}	-1.0	-5.0	mA
Gate-Source Cutoff Voltage V _{DS} = 5.0V, I _D = 1.0µA dc	V _{GS(off)}	0.75	6.0	Vdc
Magnitude of Small-Signal, Common-Source Short-Circuit Forward Transfer Admittance V _{GS} = 0, V _{DS} = 5.0V dc, f = 1.0kHz	Y _{fs2}	1,000	4,500	µmho
Small-Signal, Common-Source Short-Circuit Input Capacitance V _{GS} = 0, V _{DS} = 5.0V dc, f = 1.0MHz	C _{iss}		10	pF
Common-Source Spot Noise Figure V _{GS} = 0, V _{DS} = 5.0V dc, f = 1.0kHz B _w = 16%, R _G = 1.0 megohms e _{gen} = 1.82mV dc, R _L = 470Ω	NF		3.0	dB


**TO-18
(TO-206AA)**